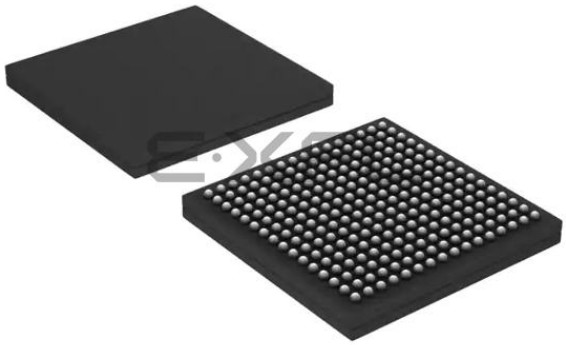

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4d
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	199
Program Memory Size	3MB (3M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 33x10b, 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	256-LBGA
Supplier Device Package	256-MAPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5646bf0mmj1

Other Features

- System clocks sources
  - 4–40 MHz external crystal oscillator
  - 16 MHz internal RC oscillator
  - FMPLL
  - Additionally, there are two low power oscillators: 128 kHz internal RC oscillator, 32 kHz external crystal oscillator
- Real Time Counter (RTC) with clock source from internal 128 kHz or 16 MHz oscillators or external 4–40 MHz crystal
  - Supports autonomous wake-up with 1 ms resolution with max timeout of 2 seconds
  - Optional support from external 32 kHz crystal oscillator, supporting wake-up with 1 second resolution and max timeout of 1 hour
- 1 Real Time Interrupt (RTI) with 32-bit counter resolution
- 1 Safety Enhanced Software Watchdog Timer (SWT) that supports keyed functionality
- 1 dual-channel FlexRay Controller with 128 message buffers
- 1 Fast Ethernet Controller (FEC)
- On-chip voltage regulator (VREG)
- Cryptographic Services Engine (CSE)
- Offered in the following standard package types:
  - 176-pin LQFP, 24 × 24 mm, 0.5 mm Lead Pitch
  - 208-pin LQFP, 28 × 28 mm, 0.5 mm Lead Pitch
  - 256-ball MAPBGA, 17 × 17mm, 1.0 mm Lead Pitch

Table 1. MPC5646C family comparison[1]

Feature	MPC5644B		MPC5644C			MPC5645B		MPC5645C			MPC5646B		MPC5646C		
Package	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA
CPU	e200z4d		e200z4d + e200z0h			e200z4d		e200z4d + e200z0h			e200z4d		e200z4d + e200z0h		
Execution speed[2]	Up to 120 MHz (e200z4d)		Up to 120 MHz (e200z4d) Up to 80 MHz (e200z0h)[3]			Up to 120 MHz (e200z4d)		Up to 120 MHz (e200z4d) Up to 80 MHz (e200z0h)[3]			Up to 120 MHz (e200z4d)		Up to 120 MHz (e200z4d) Up to 80 MHz (e200z0h)[3]		
Code flash memory	1.5 MB					2 MB					3 MB				
Data flash memory	4 x16 KB														
SRAM	128 KB		192 KB			160 KB		256 KB			192 KB		256 KB		
MPU	16-entry														
eDMA[4]	32 ch														
10-bit ADC															
dedicated[5,6]	27 ch	33 ch	27 ch	33 ch		27 ch	33 ch	27 ch	33 ch		27 ch	33 ch	27 ch	33 ch	
shared with 12-bit ADC[7]	19 ch														
12-bit ADC															
dedicated[8]	5 ch	10 ch	5 ch	10 ch		5 ch	10 ch	5 ch	10 ch		5 ch	10 ch	5 ch	10 ch	
shared with 10-bit ADC[7]	19 ch														
CTU	64 ch														
Total timer I/O[9] eMIOS	64 ch, 16-bit														
SCI (LINFlexD)	10														
SPI (DSPI)	8														
CAN (FlexCAN)[10]	6														
FlexRay	Yes														
STCU[11]	Yes														

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PA[7]	PCR[7]	AF0 AF1 AF2 AF3 — — —	GPIO[7] E0UC[7] LIN3TX — RXD[2] EIRQ[2] ADC1_S[1]	SIUL eMIOS_0 LINFlexD_3 — FEC SIUL ADC_1	I/O I/O O — I I I	M/S	Tristate	128	152	C15
PA[8]	PCR[8]	AF0 AF1 AF2 AF3 — — —	GPIO[8] E0UC[8] E0UC[14] — RXD[1] EIRQ[3] ABS[0] LIN3RX	SIUL eMIOS_0 eMIOS_0 — FEC SIUL MC_RGM LINFlexD_3	I/O I/O I/O — I I I I	M/S	Input, weak pull-up	129	153	B16
PA[9]	PCR[9]	AF0 AF1 AF2 AF3 — —	GPIO[9] E0UC[9] — CS2_1 RXD[0] FAB	SIUL eMIOS_0 — DSPI1 FEC MC_RGM	I/O I/O — O I I	M/S	Pull-down	130	154	B15
PA[10]	PCR[10]	AF0 AF1 AF2 AF3 — — —	GPIO[10] E0UC[10] SDA LIN2TX COL ADC1_S[2] SIN_1	SIUL eMIOS_0 I^2C LINFlexD_2 FEC ADC_1 DSPI_1	I/O I/O I/O O I I I	M/S	Tristate	131	155	A15
PA[11]	PCR[11]	AF0 AF1 AF2 AF3 — — — —	GPIO[11] E0UC[11] SCL — RX_ER EIRQ[16] LIN2RX ADC1_S[3]	SIUL eMIOS_0 I^2C — FEC SIUL LINFlexD_2 ADC_1	I/O I/O I/O — I I I I	M/S	Tristate	132	156	B14
PA[12]	PCR[12]	AF0 AF1 AF2 AF3 — —	GPIO[12] — E0UC[28] CS3_1 EIRQ[17] SIN_0	SIUL — eMIOS_0 DSPI1 SIUL DSPI_0	I/O — I/O O I I	S	Tristate	53	69	P6

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 — — —	GPI[49] — — — ADC0_P[5] ADC1_P[5] WKPU[28]	SIUL — — — ADC_0 ADC_1 WKPU	I — — — I I I	I	Tristate	78	94	T13
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 — —	GPI[50] — — — ADC0_P[6] ADC1_P[6]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	79	95	N11
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 — —	GPI[51] — — — ADC0_P[7] ADC1_P[7]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	80	96	R13
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 — —	GPI[52] — — — ADC0_P[8] ADC1_P[8]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	81	97	P12
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 — —	GPI[53] — — — ADC0_P[9] ADC1_P[9]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	82	98	T14
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 — —	GPI[54] — — — ADC0_P[10] ADC1_P[10]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	83	99	R14
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 — —	GPI[55] — — — ADC0_P[11] ADC1_P[11]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	84	100	P13

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PH[5]	PCR[117]	AF0 AF1 AF2 AF3 —	GPIO[117] E1UC[7] — — SIN_7	SIUL eMIOS_1 — — DSPI_7	I/O I/O — — I	S	Tristate	163	187	B7
PH[6]	PCR[118]	AF0 AF1 AF2 AF3	GPIO[118] E1UC[8] SCK_7 MA[2]	SIUL eMIOS_1 DSPI_7 ADC_0	I/O I/O I/O O	M/S	Tristate	164	188	C7
PH[7]	PCR[119]	AF0 AF1 AF2 AF3 ALT4	GPIO[119] E1UC[9] CS3_2 MA[1] CS0_7	SIUL eMIOS_1 DSPI_2 ADC_0 DSPI_7	I/O I/O O O I/O	M/S	Tristate	165	189	C6
PH[8]	PCR[120]	AF0 AF1 AF2 AF3	GPIO[120] E1UC[10] CS2_2 MA[0]	SIUL eMIOS_1 DSPI_2 ADC_0	I/O I/O O O	M/S	Tristate	166	190	A6
PH[9][6]	PCR[121]	AF0 AF1 AF2 AF3 —	GPIO[121] — — — TCK	SIUL — — — JTAGC	I/O — — — I	S	Input, weak pull-up	155	179	A11
PH[10][6]	PCR[122]	AF0 AF1 AF2 AF3 —	GPIO[122] — — — TMS	SIUL — — — JTAGC	I/O — — — I	M/S	Input, weak pull-up	148	172	D10
PH[11]	PCR[123]	AF0 AF1 AF2 AF3	GPIO[123] SOUT_3 CS0_4 E1UC[5]	SIUL DSPI_3 DSPI_4 eMIOS_1	I/O O I/O I/O	M/S	Tristate	140	164	A13
PH[12]	PCR[124]	AF0 AF1 AF2 AF3	GPIO[124] SCK_3 CS1_4 E1UC[25]	SIUL DSPI_3 DSPI_4 eMIOS_1	I/O I/O O I/O	M/S	Tristate	141	165	B12
PH[13]	PCR[125]	AF0 AF1 AF2 AF3	GPIO[125] SOUT_4 CS0_3 E1UC[26]	SIUL DSPI_4 DSPI_3 eMIOS_1	I/O O I/O I/O	M/S	Tristate	9	9	B1

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PL[10]	PCR[186]	AF0 AF1 AF2 AF3	GPIO[186] — MCKO —	SIUL — Nexus —	I/O — O —	F/S	Tristate	—	—	M11
PL[11]	PCR[187]	AF0 AF1 AF2 AF3	GPIO[187] — — —	SIUL — — —	I/O — — —	M/S	Tristate	—	—	M12
PL[12]	PCR[188]	AF0 AF1 AF2 AF3	GPIO[188] — EVTO —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	F11
PL[13]	PCR[189]	AF0 AF1 AF2 AF3	GPIO[189] — MDO6 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	F10
PL[14]	PCR[190]	AF0 AF1 AF2 AF3	GPIO[190] — MDO7 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E12
PL[15]	PCR[191]	AF0 AF1 AF2 AF3	GPIO[191] — MDO8 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E11
PM[0]	PCR[192]	AF0 AF1 AF2 AF3	GPIO[192] — MDO9 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E10
PM[1]	PCR[193]	AF0 AF1 AF2 AF3	GPIO[193] — MDO10 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E9
PM[2]	PCR[194]	AF0 AF1 AF2 AF3	GPIO[194] — MDO11 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	F12
PM[3]	PCR[195]	AF0 AF1 AF2 AF3	GPIO[195] — — —	SIUL — — —	I/O — — —	M/S	Tristate	—	—	K12

NOTE

Stresses exceeding the recommended absolute maximum ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During overload conditions ($V_{IN} > V_{DD\_HV\_A/HV\_B}$ or $V_{IN} < V_{SS\_HV}$), the voltage on pins with respect to ground (V_{SS_HV}) must not exceed the recommended values.

4.4 Recommended operating conditions

Table 9. Recommended operating conditions (3.3 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS_HV}	SR	Digital ground on VSS_HV pins	—	0	0	V
$V_{DD\_HV\_A}$[1]	SR	Voltage on $V_{DD\_HV\_A}$ pins with respect to ground (V_{SS_HV})	—	3.0	3.6	V
$V_{DD\_HV\_B}$[1]	SR	Voltage on $V_{DD\_HV\_B}$ pins with respect to ground (V_{SS_HV})	—	3.0	3.6	V
V_{SS_LV}[2]	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS_HV})	—	V_{SS_HV} – 0.1	V_{SS_HV} + 0.1	V
V_{RC_CTRL}[3]		Base control voltage for external BCP68 NPN device	Relative to V_{DD_LV}	0	V_{DD_LV} + 1	V
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC0, VSS_HV_ADC1 (ADC reference) pin with respect to ground (V_{SS_HV})	—	V_{SS_HV} – 0.1	V_{SS_HV} + 0.1	V
$V_{DD\_HV\_ADC0}$[4]	SR	Voltage on VDD_HV_ADC0 with respect to ground (V_{SS_HV})	—	3.0[5]	3.6	V
			Relative to $V_{DD\_HV\_A}$[6]	$V_{DD\_HV\_A}$ – 0.1	$V_{DD\_HV\_A}$ + 0.1	
$V_{DD\_HV\_ADC1}$[7]	SR	Voltage on VDD_HV_ADC1 with respect to ground (V_{SS_HV})	—	3.0	3.6	V
			Relative to $V_{DD\_HV\_A}$[6]	$V_{DD\_HV\_A}$ – 0.1	$V_{DD\_HV\_A}$ + 0.1	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS_HV})	—	V_{SS_HV} – 0.1	—	V
			Relative to $V_{DD\_HV\_A/HV\_B}$	—	$V_{DD\_HV\_A/HV\_B}$ + 0.1	

4.5.2 Power considerations

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using Equation 1:

$$T_J = T_A + (P_D \times R_{\theta JA}) \quad \textit{Eqn. 1}$$

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273\ °C) \quad \textit{Eqn. 2}$$

Therefore, solving equations 1 and 2:

$$K = P_D \times (T_A + 273\ °C) + R_{\theta JA} \times P_D^2 \quad \textit{Eqn. 3}$$

Where:

K is a constant for the particular part, which may be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations 1 and 2 iteratively for any value of T_A.

4.6 I/O pad electrical characteristics

4.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads—These pads are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads—These pads provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads—These pads provide maximum speed. These are used for improved Nexus debugging capability.
- Input only pads—These pads are associated to ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.
- Low power pads—These pads are active in standby mode for wakeup source.

Also, medium/slow and fast/medium pads are available in design which can be configured to behave like a slow/medium and medium/fast pads depending upon the slew-rate control.

Table 15. SLOW configuration output buffer electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1,2]		Value			Unit
						Min	Typ	Max	
V_{OL}	CC	P	Output low level SLOW configuration	Push Pull	I_{OL} = 3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	$0.1V_{DD}$	V
		C			I_{OL} = 3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(3)	—	—	$0.1V_{DD}$	
		P			I_{OL} = 1.5 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	0.5	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$.
3 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 16. MEDIUM configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions[1,2]		Value			Unit
						Min	Typ	Max	
V_{OH}	CC	C	Output high level MEDIUM configuration	Push Pull	I_{OH} = –3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	$0.8V_{DD}$	—	—	V
		C			I_{OH} = –1.5 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[3]	$0.8V_{DD}$	—	—	
		C			I_{OH} = –2 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	V_{DD} – 0.8	—	—	
V_{OL}	CC	C	Output low level MEDIUM configuration	Push Pull	I_{OL} = 3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	$0.2V_{DD}$	V
		C			I_{OL} = 1.5 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(3)	—	—	$0.1V_{DD}$	
		C			I_{OL} = 2 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	0.5	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$.
3 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

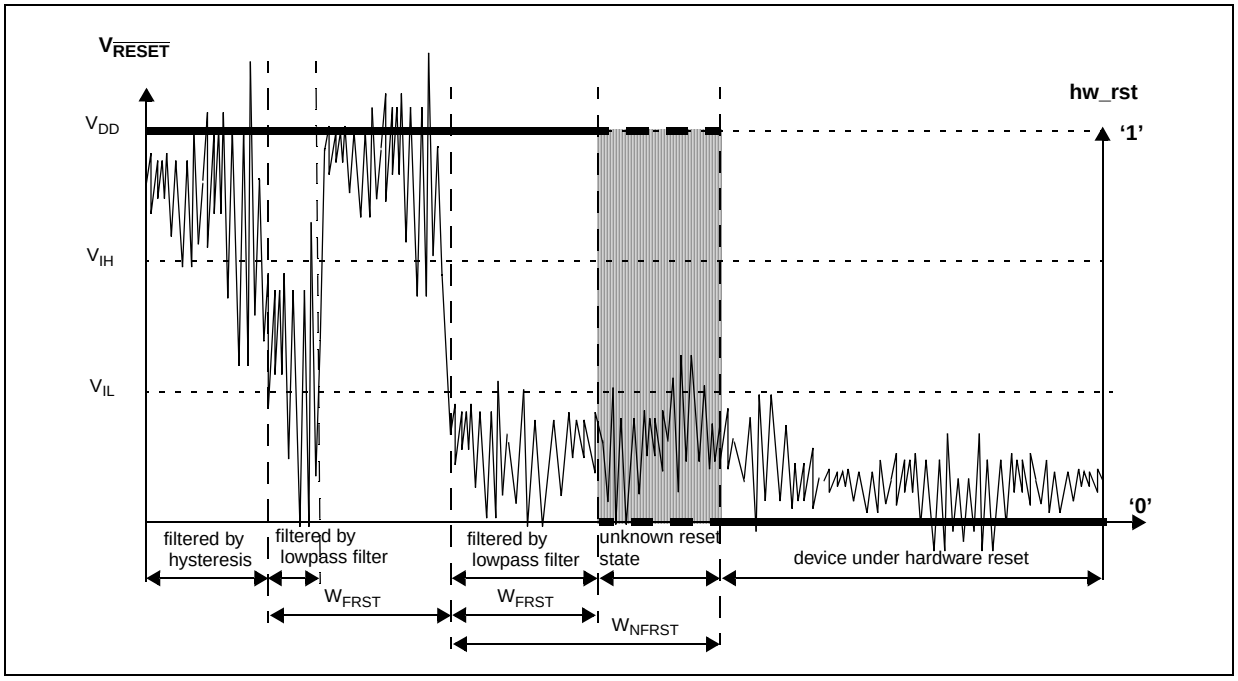

Figure 7. Noise filtering on reset signal

Table 21. Reset electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	V_{DD} + 0.4	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	—	–0.3	—	$0.35V_{DD}$	V
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	V
V_{OL}	CC	P	Output low level	Push Pull, I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
				Push Pull, I_{OL} = 1 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[3]	—	—	$0.1V_{DD}$	
				Push Pull, I_{OL} = 1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	

Table 21. Reset electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
T_{tr}	CC	D	Output transition time output pin[4] MEDIUM configuration	C_L = 25 pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	10	ns
				C_L = 50 pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	
				C_L = 100 pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	40	
				C_L = 25 pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	12	
				C_L = 50 pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	25	
				C_L = 100 pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
W_{FRST}	SR	P	Reset input filtered pulse	—	—	—	40	ns
W_{NFRST}	SR	P	Reset input not filtered pulse	—	1000	—	—	ns
$\|I_{WPU}\|$	CC	P	Weak pull-up current absolute value	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	10	—	150	µA
				V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	10	—	150	
				V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[5]	10	—	250	

NOTES:
1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$. All values need to be confirmed during device validation.
3. This is a transient configuration during power-up, up to the end of reset PHASE2 (refer to the RGM module section of the device Reference Manual).
4. C_L includes device and package capacitance (C_{PKG} < 5 pF).
5. The configuration PAD3V5 = 1 when V_{DD} = 5 V is only transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

4.8 Power management electrical characteristics

4.8.1 Voltage regulator electrical characteristics

The device implements an internal voltage regulator to generate the low voltage core supply V_{DD_LV} from the high voltage supply $V_{DD\_HV\_A}$. The following supplies are involved:

- HV: High voltage external power supply for voltage regulator module. This must be provided externally through $V_{DD\_HV\_A}$ power pin.
- LV: Low voltage internal power supply for core, FMPLL and Flash digital logic. This is generated by the on-chip VREG with an external ballast (BCP68 NPN device). It is further split into four main domains to ensure noise isolation between critical LV modules within the device:
  - LV_COR: Low voltage supply for the core. It is also used to provide supply for FMPLL through double bonding.

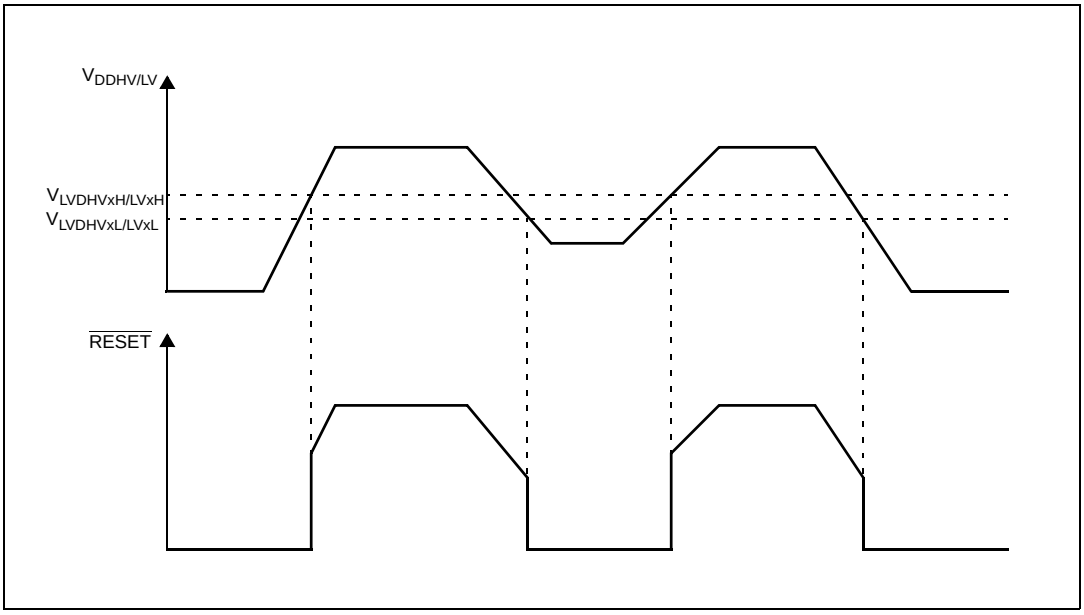

Figure 9. Low voltage monitor vs. Reset

Table 23. Low voltage monitor electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
V_{PORUP}	SR	P	Supply for functional POR module	—	1.0	—	5.5	V
V_{PORH}	CC	P	Power-on reset threshold	—	1.5	—	2.6	
$V_{LVDHV3H}$	CC	T	LVDHV3 low voltage detector high threshold	—	2.7	—	2.85	
$V_{LVDHV3L}$	CC	T	LVDHV3 low voltage detector low threshold	—	2.6	—	2.74	
$V_{LVDHV5H}$	CC	T	LVDHV5 low voltage detector high threshold	—	4.3	—	4.5	
$V_{LVDHV5L}$	CC	T	LVDHV5 low voltage detector low threshold	—	4.2	—	4.4	
$V_{LVDLVCORL}$	CC	P	LVDLVCOR low voltage detector low threshold	T_A = 25 °C, after trimming	1.12	1.145	1.17	
$V_{LVDLVBKPL}$	CC	P	LVDLVBKP low voltage detector low threshold		1.12	1.145	1.17	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 All values need to be confirmed during device validation.

4.9 Low voltage domain power consumption

Table 24 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

NOTES:
1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.
3. Data based on characterization results, not tested in production.

4.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply over-voltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

Table 33. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = 125 °C conforming to JESD 78	II level A

4.12 Fast external crystal oscillator (4–40 MHz) electrical characteristics

The device provides an oscillator/resonator driver. Figure 10 describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Table 34 provides the parameter description of 4 MHz to 40 MHz crystals used for the design simulations.

Table 40. Slow internal RC oscillator (128 kHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
T_{SIRCSU}	CC	P	Slow internal RC oscillator start-up time	T_A = 25 °C, V_{DD} = 5.0 V ± 10%	—	8	12	µs
$\Delta_{SIRCPRE}$	CC	C	Slow internal RC oscillator precision after software trimming of f_{SIRC}	T_A = 25 °C	–2	—	+2	%
$\Delta_{SIRCTRIM}$	CC	C	Slow internal RC oscillator trimming step	—	—	2.7	—	
$\Delta_{SIRCVAR}$	CC	C	Variation in f_{SIRC} across temperature and fluctuation in supply voltage, post trimming	—	–10	—	+10	%

NOTES:
1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. This does not include consumption linked to clock tree toggling and peripherals consumption when RC oscillator is ON.

4.17 ADC electrical characteristics

4.17.1 Introduction

The device provides two Successive Approximation Register (SAR) analog-to-digital converters (10-bit and 12-bit).

NOTE

Due to ADC limitations, the two ADCs cannot sample a shared channel at the same time i.e., their sampling windows cannot overlap if a shared channel is selected. If this is done, neither of the ADCs can guarantee their conversion accuracies.

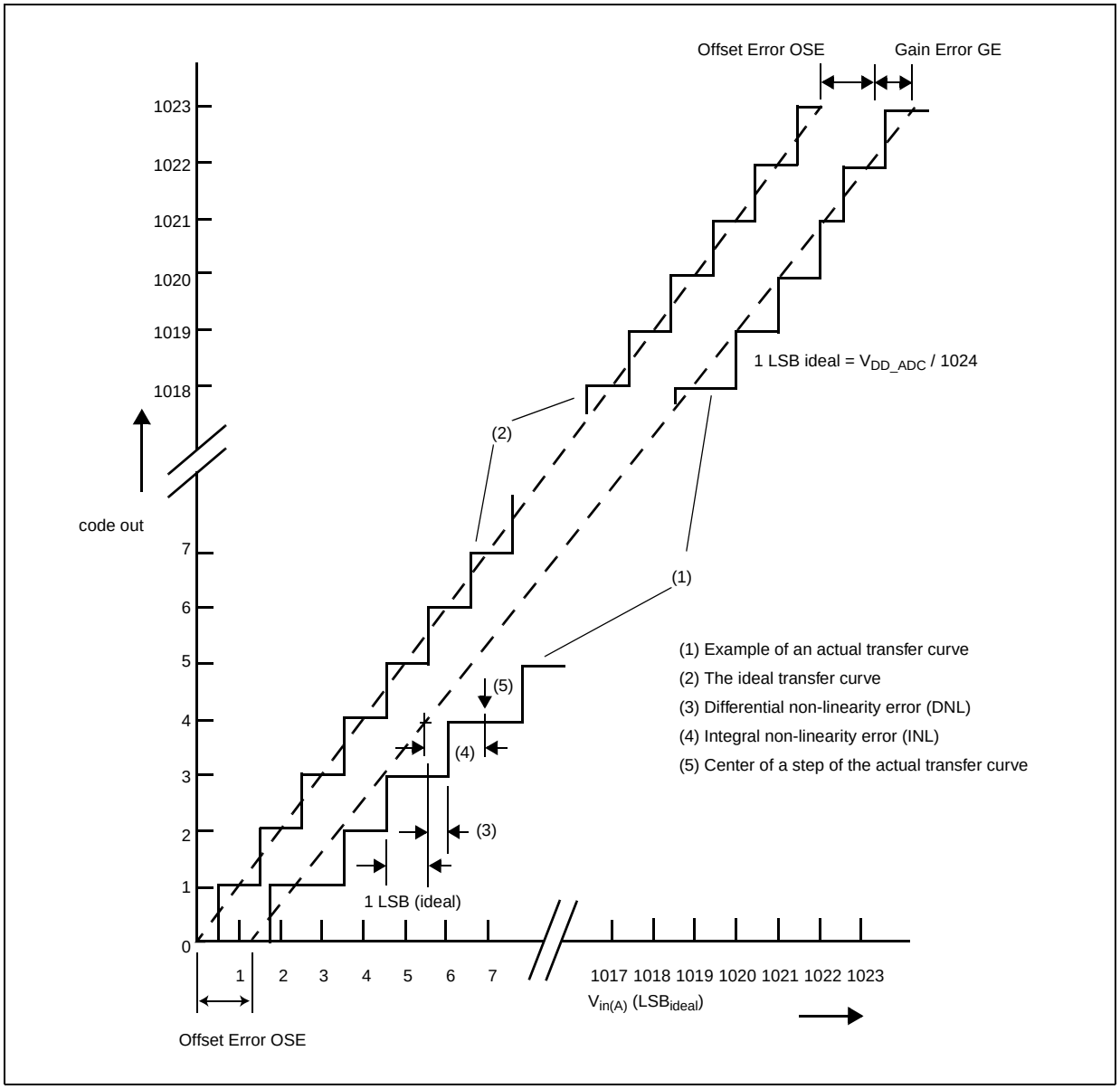

Figure 15. ADC_0 characteristic and error definitions

4.17.1.1 Input impedance and ADC accuracy

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device, can be effective: the capacitor should be as large as possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source. A real filter, can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC Filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

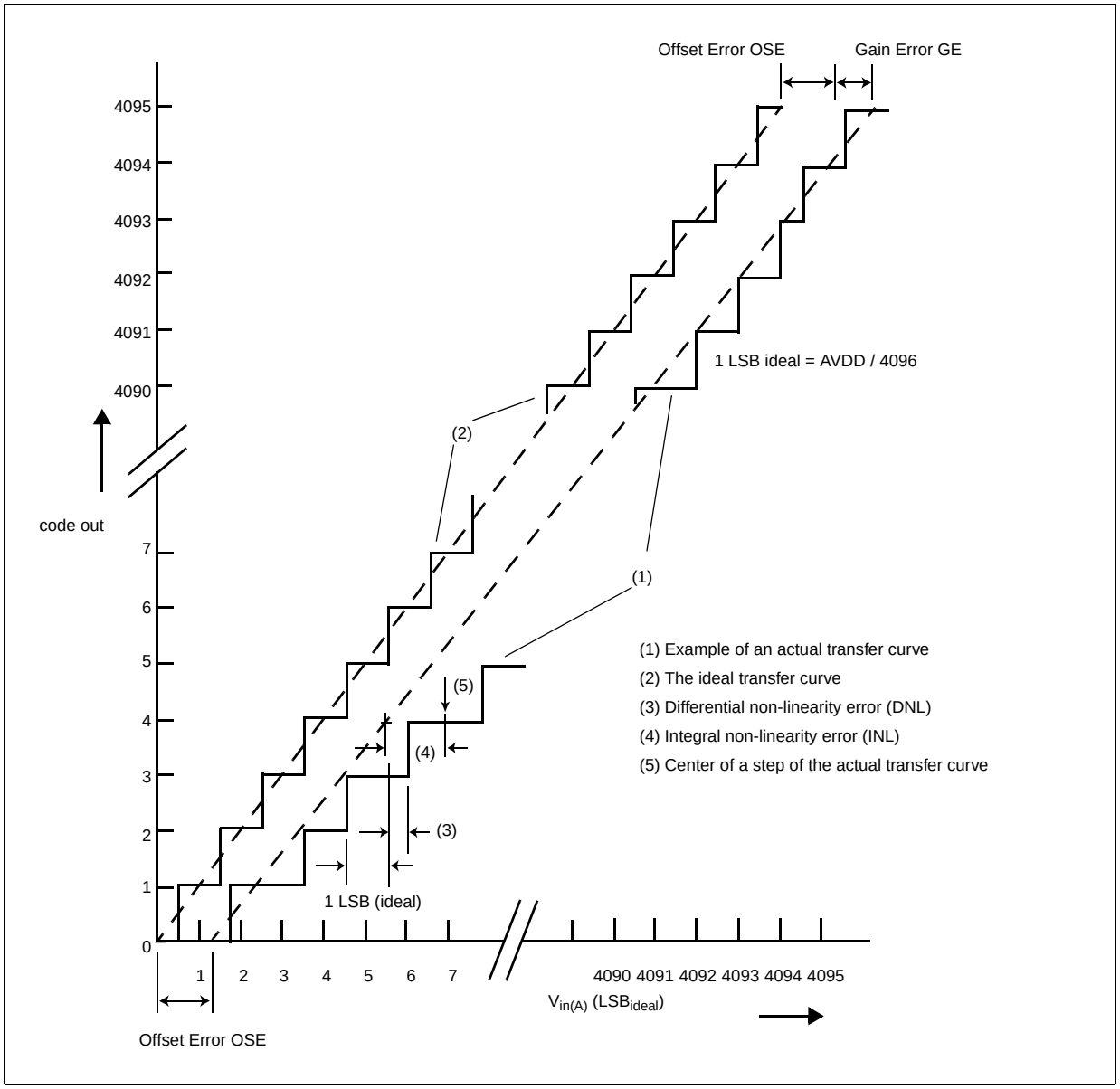

Figure 20. ADC_1 characteristic and error definitions

4.19.2 DSPI characteristics

Table 49. DSPI timing

Spec	Characteristic	Symbol	Min	Max	Unit
1	DSPI Cycle Time	t_{SCK}	Refer note[1]	—	ns
—	Internal delay between pad associated to SCK and pad associated to CSn in master mode for CSn1->0	Δt_{CSC}	—	115	ns
—	Internal delay between pad associated to SCK and pad associated to CSn in master mode for CSn1->1	Δt_{ASC}	15	—	ns
2	CS to SCK Delay[2]	t_{CSC}	7	—	ns
3	After SCK Delay[3]	t_{ASC}	15	—	ns
4	SCK Duty Cycle	t_{SDC}	$0.4 \times t_{SCK}$	$0.6 \times t_{SCK}$	ns
—	Slave Setup Time ($\overline{SS}$ active to SCK setup time)	t_{SUSS}	5	—	ns
—	Slave Hold Time ($\overline{SS}$ active to SCK hold time)	t_{HSS}	10	—	ns
5	Slave Access Time ($\overline{SS}$ active to SOUT valid)[4]	t_A	—	42	ns
6	Slave SOUT Disable Time ($\overline{SS}$ inactive to SOUT High-Z or invalid)	t_{DIS}	—	25	ns
7	CSx to $\overline{PCSS}$ time	t_{PCSC}	0	—	ns
8	$\overline{PCSS}$ to PCSx time	t_{PASC}	0	—	ns

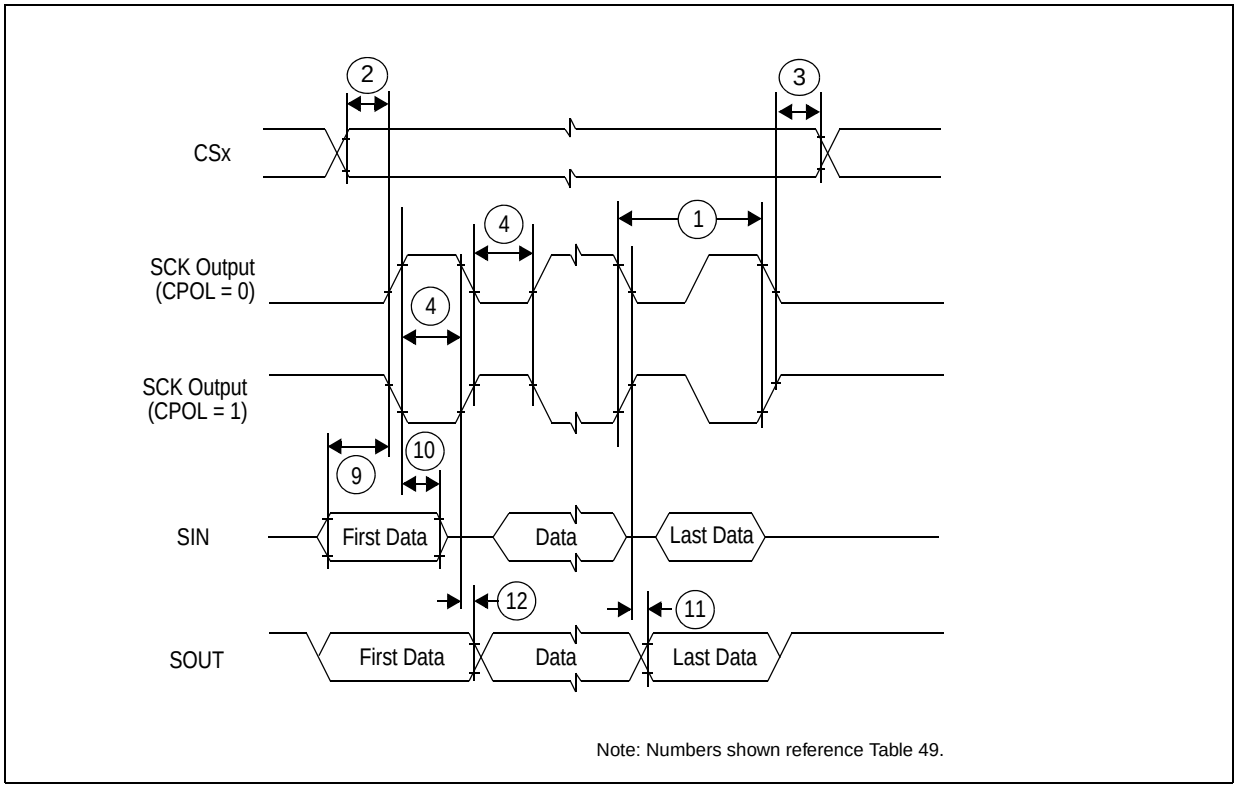

Figure 25. DSPI classic SPI timing–master, CPHA = 0

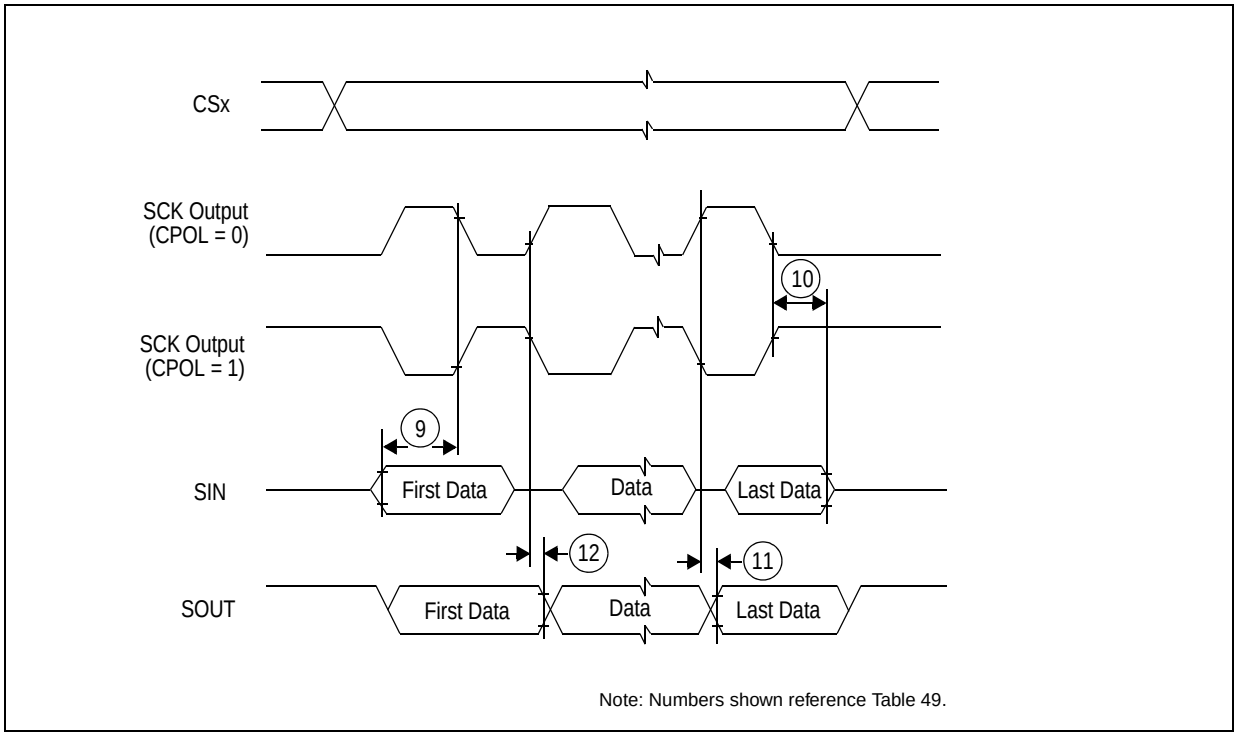

Figure 26. DSPI classic SPI timing–master, CPHA = 1

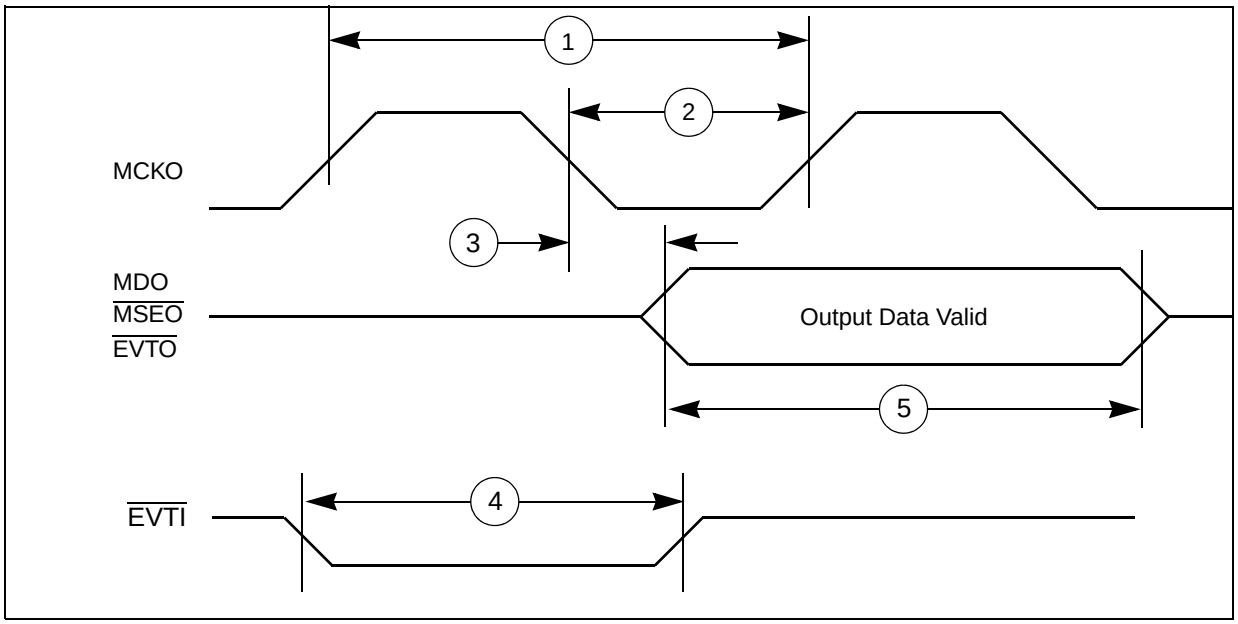

Figure 34. Nexus output timing

5 Package characteristics

5.1 Package mechanical data

5.1.1 176 LQFP package mechanical drawing